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Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.2GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8548hxatg

4 Input Clocks

This section discusses the timing for the input clocks.

4.1 System Clock Timing

The following table provides the system clock (SYSCLK) AC timing specifications for the device.

Table 5. SYSCLK AC Timing Specifications

At recommended operating conditions (see Table 2) with $OV_{DD} = 3.3\text{ V} \pm 165\text{ mV}$.

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	16	—	133	MHz	1, 6, 7, 8
SYSCLK cycle time	t_{SYSCLK}	7.5	—	60	ns	6, 7, 8
SYSCLK rise and fall time	$t_{\text{KH}}, t_{\text{KL}}$	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	$t_{\text{KHK}}/t_{\text{SYSCLK}}$	40	—	60	%	3
SYSCLK jitter	—	—	—	± 150	ps	4, 5

Notes:

- Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.
- Rise and fall times for SYSCLK are measured at 0.6 and 2.7 V.
- Timing is guaranteed by design and characterization.
- This represents the total input jitter—short term and long term—and is guaranteed by design.
- The SYSCLK driver’s closed loop jitter bandwidth must be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter.
- This parameter has been adjusted slower according to the workaround for device erratum GEN 13.
- For spread spectrum clocking. Guidelines are +0% to –1% down spread at modulation rate between 20 and 60 kHz on SYSCLK.
- System with operating core frequency less than 1200 MHz must limit SYSCLK frequency to 100 MHz maximum.

4.2 Real Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal must be greater than 2x the period of the CCB clock. That is, minimum clock high time is $2 \times t_{\text{CCB}}$, and minimum clock low time is $2 \times t_{\text{CCB}}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that $GV_{DD}(\text{typ}) = 2.5 \text{ V}$ for DDR SDRAM, and $GV_{DD}(\text{typ}) = 1.8 \text{ V}$ for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 11. DDR2 SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	-50	50	μA	4
Output high current ($V_{OUT} = 1.420 \text{ V}$)	I_{OH}	-13.4	—	mA	—
Output low current ($V_{OUT} = 0.280 \text{ V}$)	I_{OL}	13.4	—	mA	—

Notes:

- GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
- MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed $\pm 2\%$ of the DC value.
- V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF} . This rail must track variations in the DC level of MV_{REF} .
- Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

This table provides the DDR2 I/O capacitance when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 12. DDR2 SDRAM Capacitance for $GV_{DD}(\text{typ})=1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, \overline{DQS}	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, \overline{DQS}	C_{DIO}	—	0.5	pF	1

Note:

- This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, $f = 1 \text{ MHz}$, $T_A = 25^\circ\text{C}$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

8 Enhanced Three-Speed Ethernet (eTSEC)

This section provides the AC and DC electrical characteristics for the enhanced three-speed Ethernet controller. The electrical characteristics for MDIO and MDC are specified in [Section 9, “Ethernet Management Interface Electrical Characteristics.”](#)

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1Gb Mbps)—GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics

The electrical characteristics specified here apply to all gigabit media independent interface (GMII), media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), and reduced media independent interface (RMII) signals except management data input/output (MDIO) and management data clock (MDC). The RGMII and RTBI interfaces are defined for 2.5 V, while the GMII, MII, and TBI interfaces can be operated at 3.3 or 2.5 V. The GMII, MII, or TBI interface timing is compliant with the IEEE 802.3. The RGMII and RTBI interfaces follow the *Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3* (12/10/2000). The RMII interface follows the *RMII Consortium RMII Specification Version 1.2* (3/20/1998). The electrical characteristics for MDIO and MDC are specified in [Section 9, “Ethernet Management Interface Electrical Characteristics.”](#)

8.1.1 eTSEC DC Electrical Characteristics

All GMII, MII, TBI, RGMII, RMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in [Table 22](#) and [Table 23](#). The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 22. GMII, MII, RMII, and TBI DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	V_{DD} V_{DD}	3.13	3.47	V	1, 2
Output high voltage ($V_{DD}/V_{DD} = \min$, $I_{OH} = -4.0$ mA)	V_{OH}	2.40	$V_{DD}/V_{DD} + 0.3$	V	—
Output low voltage ($V_{DD}/V_{DD} = \min$, $I_{OL} = 4.0$ mA)	V_{OL}	GND	0.50	V	—
Input high voltage	V_{IH}	2.0	$V_{DD}/V_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	0.90	V	—
Input high current ($V_{IN} = V_{DD}$, $V_{IN} = V_{DD}$)	I_{IH}	—	40	μ A	1, 2, 3
Input low current ($V_{IN} = \text{GND}$)	I_{IL}	-600	—	μ A	—

Notes:

1. V_{DD} supports eTSECs 1 and 2.
2. V_{DD} supports eTSECs 3 and 4.
3. The symbol V_{IN} , in this case, represents the V_{IN} and V_{IN} symbols referenced in [Table 1](#) and [Table 2](#).

Table 23. GMII, MII, RMII, TBI, RGMII, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.37	2.63	V	1, 2
Output high voltage ($LV_{DD}/TV_{DD} = \text{Min}$, $I_{OH} = -1.0 \text{ mA}$)	V_{OH}	2.00	$LV_{DD}/TV_{DD} + 0.3$	V	—
Output low voltage ($LV_{DD}/TV_{DD} = \text{Min}$, $I_{OL} = 1.0 \text{ mA}$)	V_{OL}	GND -0.3	0.40	V	—
Input high voltage	V_{IH}	1.70	$LV_{DD}/TV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	0.90	V	—
Input high current ($V_{IN} = LV_{DD}$, $V_{IN} = TV_{DD}$)	I_{IH}	—	10	μA	1, 2, 3
Input low current ($V_{IN} = \text{GND}$)	I_{IL}	-15	—	μA	3

Notes:

1. LV_{DD} supports eTSECs 1 and 2.
2. TV_{DD} supports eTSECs 3 and 4.
3. Note that the symbol V_{IN} , in this case, represents the LV_{IN} and TV_{IN} symbols referenced in [Table 1](#) and [Table 2](#).

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performances and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC n 's TSEC n _TX_CLK, while the receive clock must be applied to pin TSEC n _RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back out onto the TSEC n _GTX_CLK pin (while transmit data appears on TSEC n _TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC n _GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, since the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is relationship between the maximum FIFO speed and the platform speed. For more information see [Section 4.5, "Platform to FIFO Restrictions."](#)

Figure 17 shows the RGMII and RTBI AC timing and multiplexing diagrams.

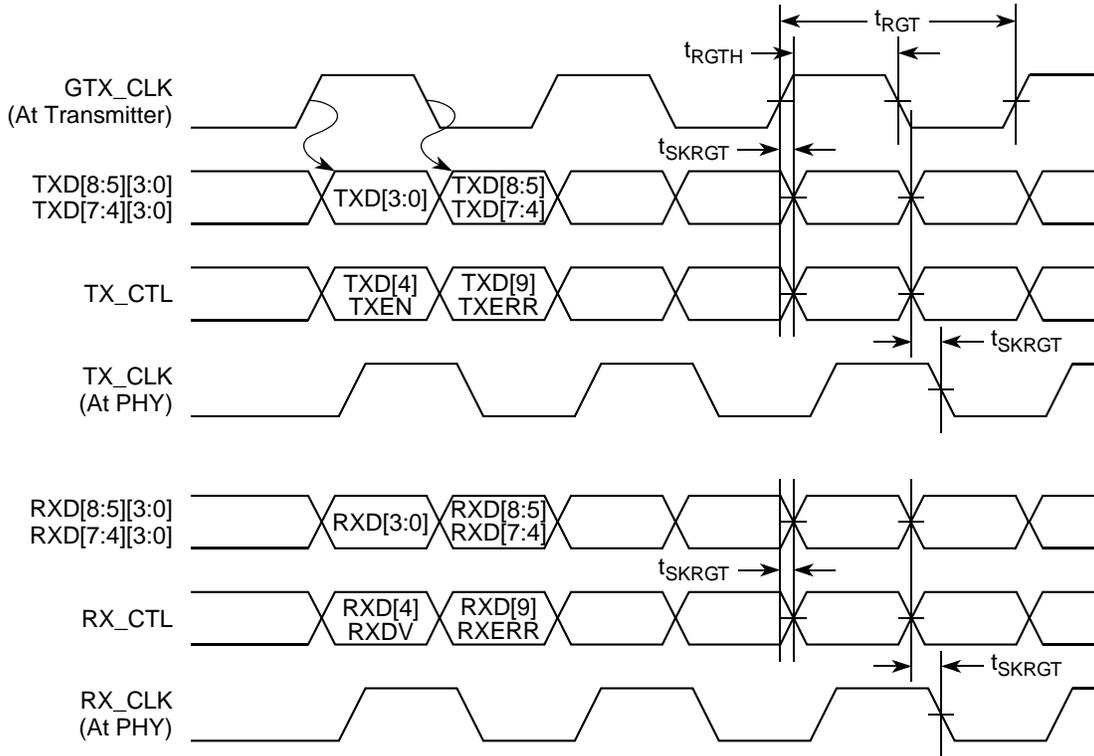


Figure 17. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.2.7 RGMII AC Timing Specifications

This section describes the RGMII transmit and receive AC timing specifications.

8.2.7.1 RGMII Transmit AC Timing Specifications

The RGMII transmit AC timing specifications are in this table.

Table 34. RGMII Transmit AC Timing Specifications

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TSEC _n _TX_CLK clock period	t_{RMT}	15.0	20.0	25.0	ns
TSEC _n _TX_CLK duty cycle	t_{RMTH}	35	50	65	%
TSEC _n _TX_CLK peak-to-peak jitter	t_{RMTJ}	—	—	250	ps
Rise time TSEC _n _TX_CLK (20%–80%)	t_{RMTR}	1.0	—	2.0	ns
Fall time TSEC _n _TX_CLK (80%–20%)	t_{RMTF}	1.0	—	2.0	ns

Table 34. RMIIT Transmit AC Timing Specifications (continued)

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TSEC _n _TX_CLK to RMIIT data TXD[1:0], TX_EN delay	t _{RMTDX}	1.0	—	10.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 18 shows the RMIIT transmit AC timing diagram.

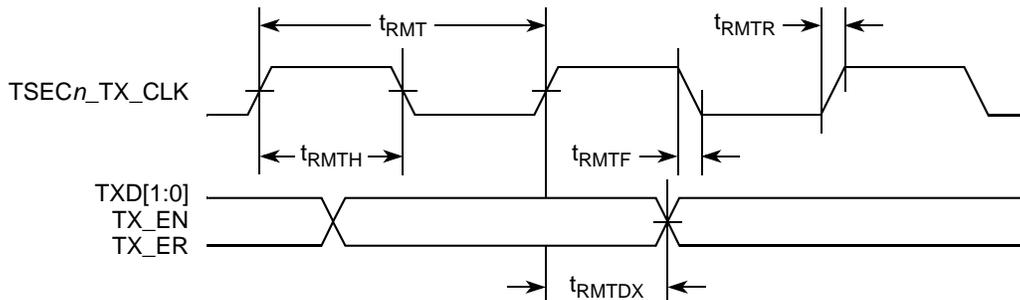


Figure 18. RMIIT Transmit AC Timing Diagram

8.2.7.2 RMIIT Receive AC Timing Specifications

Table 35. RMIIT Receive AC Timing Specifications

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TSEC _n _TX_CLK clock period	t _{RMR}	15.0	20.0	25.0	ns
TSEC _n _TX_CLK duty cycle	t _{RMRH}	35	50	65	%
TSEC _n _TX_CLK peak-to-peak jitter	t _{RMRJ}	—	—	250	ps
Rise time TSEC _n _TX_CLK(20%–80%)	t _{RMRR}	1.0	—	2.0	ns
Fall time TSEC _n _TX_CLK (80%–20%)	t _{RMRF}	1.0	—	2.0	ns
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK rising edge	t _{RMRDV}	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK rising edge	t _{RMRDV}	2.0	—	—	ns

Note:

1. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

10.2 Local Bus AC Electrical Specifications

This table describes the timing parameters of the local bus interface at $BV_{DD} = 3.3$ V. For information about the frequency range of local bus, see [Section 20.1, “Clock Ranges.”](#)

Table 40. Local Bus Timing Parameters ($BV_{DD} = 3.3$ V)—PLL Enabled

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{LGTA}/LUPWAIT$)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{LGTA}/LUPWAIT$ input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{LGTA}/LUPWAIT$)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{LGTA}/LUPWAIT$ input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
- All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
- All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
- Input timings are measured at the pin.
- For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
- Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
- Guaranteed by design.

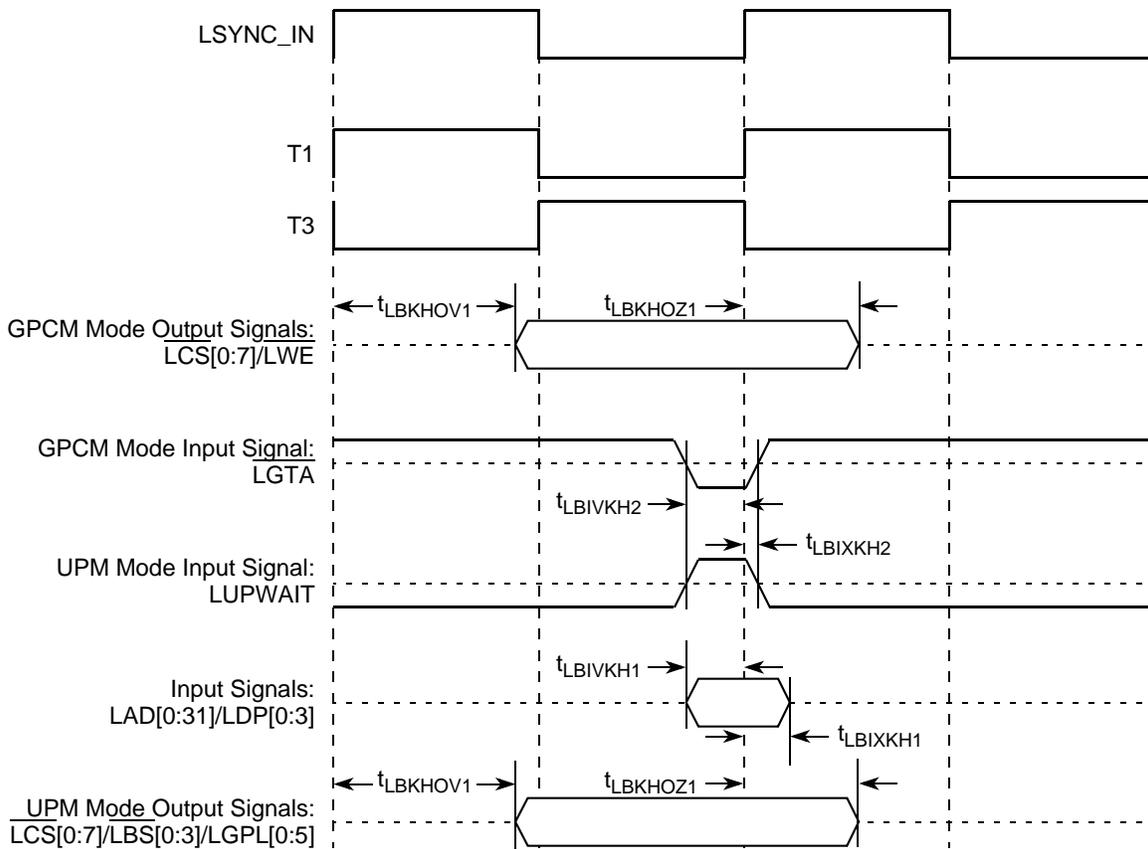


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Enabled)

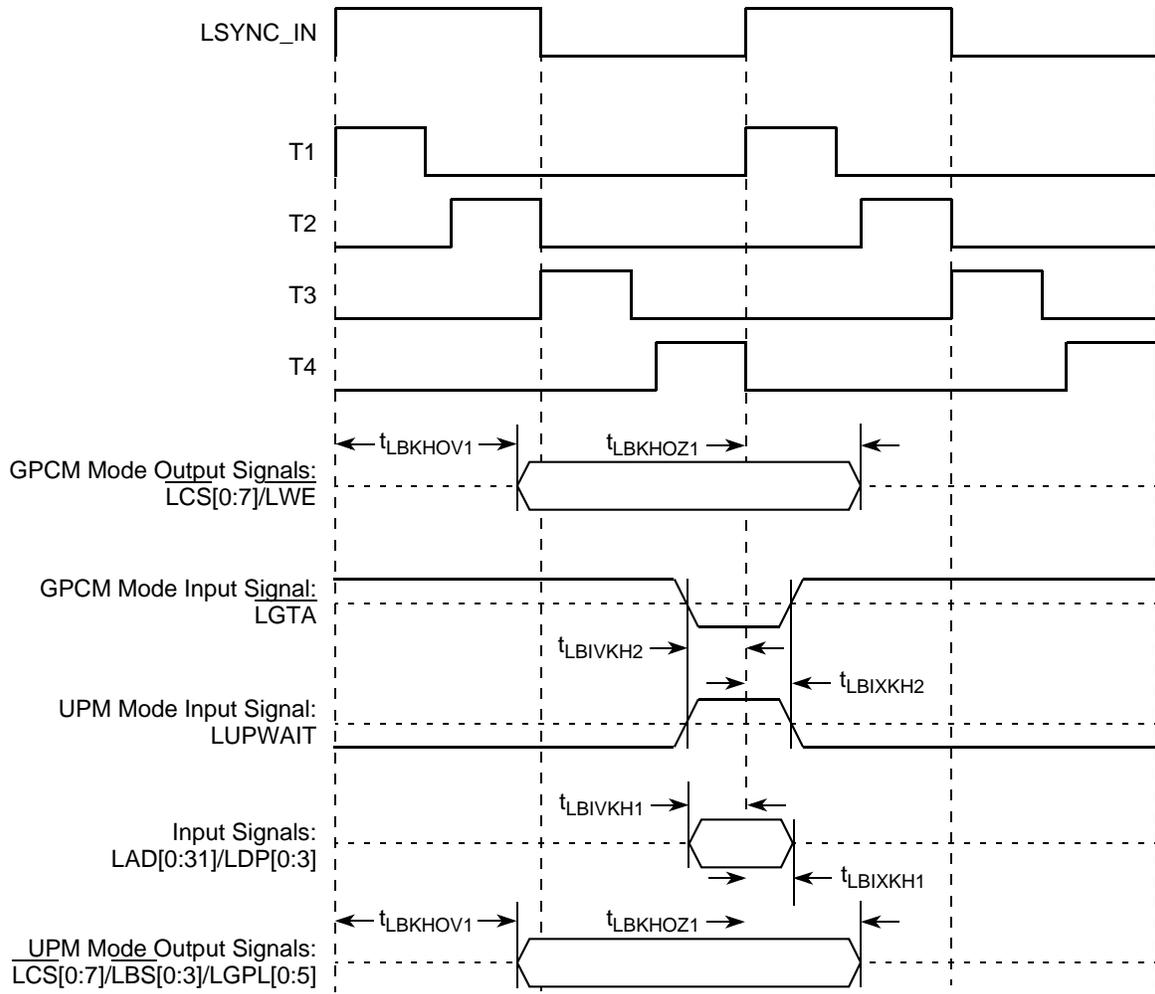


Figure 27. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Enabled)

- The SD_REF_CLK and $\overline{\text{SD_REF_CLK}}$ are internally AC-coupled differential inputs as shown in Figure 39. Each differential clock input (SD_REF_CLK or $\overline{\text{SD_REF_CLK}}$) has a 50- Ω termination to SGND_SRDS $_n$ (xcorevss) followed by on-chip AC-coupling.
- The external reference clock driver must be able to drive this termination.
- The SerDes reference clock input can be either differential or single-ended. See the differential mode and single-ended mode description below for further detailed requirements.
- The maximum average current requirement that also determines the common mode voltage range:
 - When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8 mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (see the following bullet for more detail), since the input is AC-coupled on-chip.
 - This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V/50 = 8 mA) while the minimum common mode input level is 0.1 V above SGND_SRDS $_n$ (xcorevss). For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0 to 16 mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400 mV.
 - If the device driving the SD_REF_CLK and $\overline{\text{SD_REF_CLK}}$ inputs cannot drive 50 Ω to SGND_SRDS $_n$ (xcorevss) DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.
- The input amplitude requirement:
 - This requirement is described in detail in the following sections.

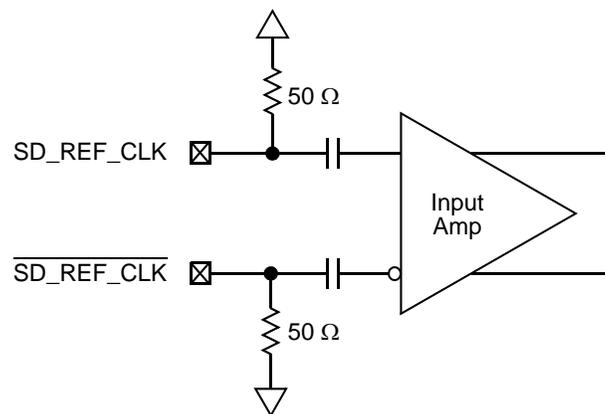


Figure 39. Receiver of SerDes Reference Clocks

16.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below:

- Differential mode

17 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the MPC8548E.

17.1 DC Requirements for PCI Express SD_REF_CLK and SD_REF_CLK

For more information, see [Section 16.2, “SerDes Reference Clocks.”](#)

17.2 AC Requirements for PCI Express SerDes Clocks

[Table 55](#) lists the AC requirements for the PCI Express SerDes clocks.

Table 55. SD_REF_CLK and SD_REF_CLK AC Requirements

Symbol	Parameter Description	Min	Typ	Max	Unit	Notes
t_{REF}	REFCLK cycle time	—	10	—	ns	1
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles.	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location.	-50	—	50	ps	—

Note:

1. Typical based on *PCI Express Specification 2.0*.

17.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million (ppm) of each other at all times. This is specified to allow bit rate clock sources with a ± 300 ppm tolerance.

17.4 Physical Layer Specifications

The following is a summary of the specifications for the physical layer of PCI Express on this device. For further details as well as the specifications of the transport and data link layer see *PCI Express Base Specification, Rev. 1.0a*.

17.4.1 Differential Transmitter (TX) Output

[Table 56](#) defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

Table 56. Differential Transmitter (TX) Output Specifications (continued)

Symbol	Parameter	Min	Nom	Max	Unit	Comments
$T_{\text{crosslink}}$	Crosslink random timeout	0	—	1	ms	This random timeout helps resolve conflicts in crosslink configuration by eventually resulting in only one downstream and one upstream port. See Note 7.

Notes:

1. No test load is necessarily associated with this value.
2. Specified at the measurement point into a timing and voltage compliance test load as shown in [Figure 50](#) and measured over any 250 consecutive TX UIs. (Also see the transmitter compliance eye diagram shown in [Figure 48](#).)
3. A $T_{\text{TX-EYE}} = 0.70$ UI provides for a total sum of deterministic and random jitter budget of $T_{\text{TX-JITTER-MAX}} = 0.30$ UI for the transmitter collected over any 250 consecutive TX UIs. The $T_{\text{TX-EYE-MEDIAN-to-MAX-JITTER}}$ median is less than half of the total TX jitter budget collected over any 250 consecutive TX UIs. Note that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value.
4. The transmitter input impedance shall result in a differential return loss greater than or equal to 12 dB and a common mode return loss greater than or equal to 6 dB over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50- Ω probes—see [Figure 50](#)). Note that the series capacitors C_{TX} is optional for the return loss measurement.
5. Measured between 20%–80% at transmitter package pins into a test load as shown in [Figure 50](#) for both $V_{\text{TX-D+}}$ and $V_{\text{TX-D-}}$.
6. See Section 4.3.1.8 of the *PCI Express Base Specifications Rev 1.0a*.
7. See Section 4.2.6.3 of the *PCI Express Base Specifications Rev 1.0a*.
8. MPC8548E SerDes transmitter does not have CTX built in. An external AC coupling capacitor is required.

17.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in [Figure 48](#) is specified using the passive compliance/test measurement load (see [Figure 50](#)) in place of any real PCI Express interconnect +RX component.

There are two eye diagrams that must be met for the transmitter. Both eye diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams differ in voltage depending whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit is always relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (for example, least squares and median deviation fits).

Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Parallelism measurement shall exclude any effect of mark on top surface of package.
6. All dimensions are symmetric across the package center lines unless dimensioned otherwise.

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PCI1_REQ}}[4:1]$	AH2, AG4, AG3, AH4	I	OV_{DD}	— — — — —
$\overline{\text{PCI1_REQ0}}$	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
$\overline{\text{PCI1_DEVSEL}}$	AH11	I/O	OV_{DD}	2
$\overline{\text{PCI1_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
$\overline{\text{PCI1_REQ64/PCI2_FRAME}}$	AF14	I/O	OV_{DD}	2, 5, 10
$\overline{\text{PCI1_ACK64/PCI2_DEVSEL}}$	V15	I/O	OV_{DD}	2
PCI2_CLK	AE28	I	OV_{DD}	39
$\overline{\text{PCI2_IRDY}}$	AD26	I/O	OV_{DD}	2
$\overline{\text{PCI2_PERR}}$	AD25	I/O	OV_{DD}	2
$\overline{\text{PCI2_GNT}}[4:1]$	AE26, AG24, AF25, AE25	O	OV_{DD}	5, 9, 35
$\overline{\text{PCI2_GNT0}}$	AG25	I/O	OV_{DD}	—
$\overline{\text{PCI2_SERR}}$	AD24	I/O	OV_{DD}	2, 4
$\overline{\text{PCI2_STOP}}$	AF24	I/O	OV_{DD}	2
$\overline{\text{PCI2_TRDY}}$	AD27	I/O	OV_{DD}	2
$\overline{\text{PCI2_REQ}}[4:1]$	AD28, AE27, W17, AF26	I	OV_{DD}	—
$\overline{\text{PCI2_REQ0}}$	AH25	I/O	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}[0:8]$	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—

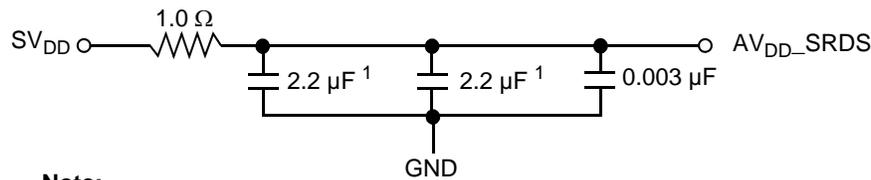
Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Reserved	AE26	—	—	2
cfg_pci1_clk	AG24	I	OV _{DD}	5
Reserved	AF25	—	—	101
Reserved	AE25	—	—	2
Reserved	AG25	—	—	2
Reserved	AD24	—	—	2
Reserved	AF24	—	—	2
Reserved	AD27	—	—	2
Reserved	AD28, AE27, W17, AF26	—	—	2
Reserved	AH25	—	—	2
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV _{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV _{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV _{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV _{DD}	—
$\overline{\text{MDQS}}$ [0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV _{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV _{DD}	—
MBA[0:2]	F7, J7, M11	O	GV _{DD}	—
$\overline{\text{MWE}}$	E7	O	GV _{DD}	—
$\overline{\text{MCAS}}$	H7	O	GV _{DD}	—
$\overline{\text{MRAS}}$	L8	O	GV _{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV _{DD}	11
$\overline{\text{MCS}}$ [0:3]	K8, J8, G8, F8	O	GV _{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV _{DD}	—
$\overline{\text{MCK}}$ [0:5]	J9, A15, G1, L9, B14, F2	O	GV _{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV _{DD}	—
MDIC[0:1]	A19, B19	I/O	GV _{DD}	36

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
IIC1_SDA	AG21	I/O	OV _{DD}	4, 27
IIC2_SCL	AG15	I/O	OV _{DD}	4, 27
IIC2_SDA	AG14	I/O	OV _{DD}	4, 27
SerDes				
SD_RX[0:7]	M28, N26, P28, R26, W26, Y28, AA26, AB28	I	XV _{DD}	—
$\overline{\text{SD_RX}}[0:7]$	M27, N25, P27, R25, W25, Y27, AA25, AB27	I	XV _{DD}	—
SD_TX[0:7]	M22, N20, P22, R20, U20, V22, W20, Y22	O	XV _{DD}	—
$\overline{\text{SD_TX}}[0:7]$	M23, N21, P23, R21, U21, V23, W21, Y23	O	XV _{DD}	—
SD_PLL_TPD	U28	O	XV _{DD}	24
SD_REF_CLK	T28	I	XV _{DD}	—
$\overline{\text{SD_REF_CLK}}$	T27	I	XV _{DD}	—
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV _{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG17	I	OV _{DD}	—
$\overline{\text{HRESET_REQ}}$	AG16	O	OV _{DD}	29
$\overline{\text{SRESET}}$	AG20	I	OV _{DD}	—
$\overline{\text{CKSTP_IN}}$	AA9	I	OV _{DD}	—
$\overline{\text{CKSTP_OUT}}$	AA8	O	OV _{DD}	2, 4
Debug				
TRIG_IN	AB2	I	OV _{DD}	—
TRIG_OUT/READY/QUIESCE	AB1	O	OV _{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV _{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV _{DD}	6, 19, 29
MDVAL	AE5	O	OV _{DD}	6
CLK_OUT	AE21	O	OV _{DD}	11
Clock				
RTC	AF16	I	OV _{DD}	—
SYSClk	AH17	I	OV _{DD}	—

the ground plane. Use ceramic chip capacitors with the highest possible self-resonant frequency. All traces must be kept short, wide and direct.

**Note:**

1. An 0805 sized capacitor is recommended for system initial bring-up.

Figure 60. SerDes PLL Power Supply Filter

Note the following:

- $AV_{DD-SRDS}$ must be a filtered version of SV_{DD} .
- Signals on the SerDes interface are fed from the XV_{DD} power plane.

22.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the device system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} pin of the device. These decoupling capacitors must receive their power from separate V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , LV_{DD} , and GND power planes in the PCB, utilizing short low impedance traces to minimize inductance. Capacitors must be placed directly under the device using a standard escape pattern as much as possible. If some caps are to be placed surrounding the part it must be routed with large trace to minimize the inductance.

These capacitors must have a value of 0.1 μF . Only ceramic SMT (surface mount technology) capacitors must be used to minimize lead inductance, preferably 0402 or 0603 sizes. Besides, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors must have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They must also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 μF (AVX TPS tantalum or Sanyo OSCON). However, customers must work directly with their power regulator vendor for best values, types and quantity of bulk capacitors.

22.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors must be used to minimize inductance. Connections from all capacitors to power and ground must be done with multiple vias to further reduce inductance.

as shown in [Figure 63](#). If this is not possible, the isolation resistor allows future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.

- No pull-up/pull-down is required for TDI, TMS, TDO, or TCK.

COP_TDO	1	2	NC
COP_TDI	3	4	$\overline{\text{COP_TRST}}$
COP_RUN/STOP	5	6	COP_VDD_SENSE
COP_TCK	7	8	$\overline{\text{COP_CHKSTP_IN}}$
COP_TMS	9	10	NC
$\overline{\text{COP_SRESET}}$	11	12	NC
$\overline{\text{COP_HRESET}}$	13	KEY No pin	
$\overline{\text{COP_CHKSTP_OUT}}$	15	16	GND

Figure 62. COP Connector Physical Pinout

- $\overline{\text{SD_REF_CLK}}$

NOTE

It is recommended to power down the unused lane through SRDSCR1[0:7] register (offset = 0xE_0F08) (this prevents the oscillations and holds the receiver output in a fixed state) that maps to SERDES lane 0 to lane 7 accordingly.

Pins V28 and M26 must be tied to XV_{DD} . Pins V27 and M25 must be tied to GND through a 300- Ω resistor.

22.11 Guideline for PCI Interface Termination

PCI termination if PCI 1 or PCI 2 is not used at all.

Option 1

If PCI arbiter is enabled during POR:

- All AD pins are driven to the stable states after POR. Therefore, all ADs pins can be floating.
- All PCI control pins can be grouped together and tied to OV_{DD} through a single 10-k Ω resistor.
- It is optional to disable PCI block through DEVDISR register after POR reset.

Option 2

If PCI arbiter is disabled during POR:

- All AD pins are in the input state. Therefore, all ADs pins need to be grouped together and tied to OV_{DD} through a single (or multiple) 10-k Ω resistor(s).
- All PCI control pins can be grouped together and tied to OV_{DD} through a single 10-k Ω resistor.
- It is optional to disable PCI block through DEVDISR register after POR reset.

22.12 Guideline for LBIU Termination

If the LBIU parity pins are not used, the following is the termination recommendation:

- For LDP[0:3]—tie them to ground or the power supply rail via a 4.7-k Ω resistor.
- For LPBSE—tie it to the power supply rail via a 4.7-k Ω resistor (pull-up resistor).